

16 K × 4 High Speed CMOS SRAM

Short description. Please refer to the full datasheet available on TEMIC web for detailed technical information.

Introduction

The HM 65788 is a high speed CMOS static RAM organized as 16384 × 4 bits. It is manufactured using TEMIC's high performance CMOS technology.

Access times as fast as 15 ns are available with maximum power consumption of only 633 mW.

The HM 65788 features fully static operation requiring no external clocks or timing strobes. The automatic power-down feature reduces the power consumption by 60 % when the circuit is deselected.

Easy memory expansion is provided by an active low chip select (\overline{CS}) and three state drivers.

All inputs and outputs of the HM 65788 are TTL compatible and operate from single 5 V supply thus simplifying system design.

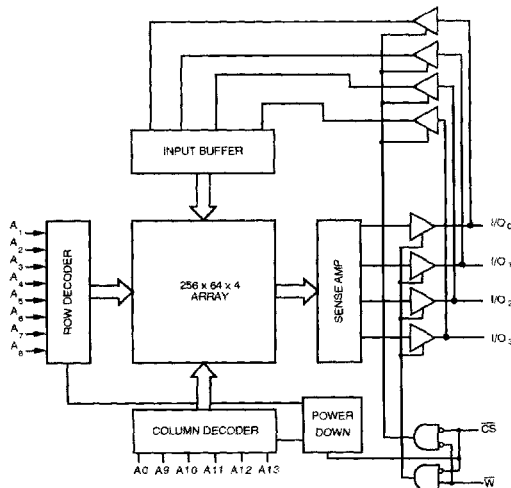
The HM 65788 is 100 % processed following the test methods of MIL STD 883 making it ideally suitable for military applications that demand superior levels of performance and reliability.

Features

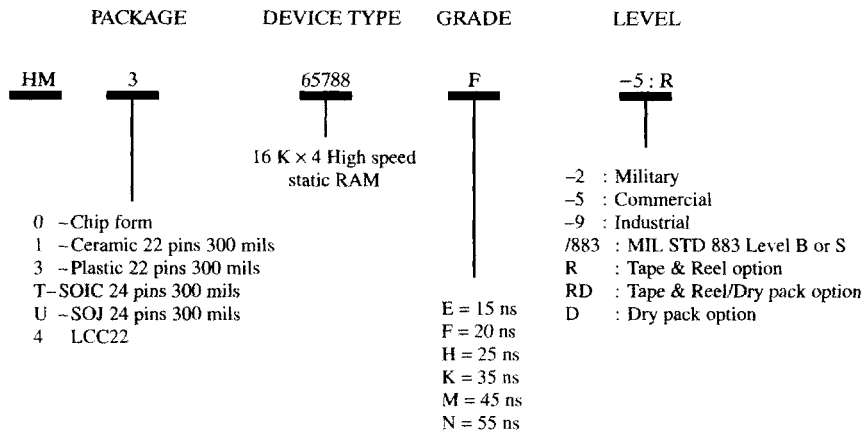
- Fast access time
 - Commercial : 15/20/25/35/45/55 ns
 - Industrial/military : 20/25/35/45/55 ns
- Low power consumption
 - Active : 267 mW (typ)
 - Standby : 75 mW (typ)
- Wide temperature range :
 - 55°C to + 125°C
- 300 mils width package
- TTL compatible inputs and outputs
- Asynchronous
- Capable of withstanding greater than 2000 V electrostatic discharge
- Single 5 volt supply

Interface

Block Diagram



Ordering Information



Military Version

The following table gives package/access time/process flow available combinations

Temp. range	Packages	Access Time (ns)					Std process 65788 Mil flows (including SMD5962-89692 SMD5962-86859)
		20 (F)	25 (H)	35 (K)	45 (M)	55 (N)	
M	1 4 0	• • X	• • X	• • X	• • X	• • •	• • •

• = product in production

X = call sales office for availability

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